

## FAN7383 Half-Bridge Gate-Drive IC

### Features

- Floating Channel Designed for Bootstrap Operation to +600V.
- Typically 350mA/650mA Sourcing/Sinking Current Driving Capability for Both Channels
- Extended Allowable Negative V<sub>S</sub> Swing to -9.8V for Signal Propagation at V<sub>DD</sub>=V<sub>BS</sub>=15V
- High-Side Output in Phase of IN Signal
- Built-in UVLO Functions for Both Channels
- Built-in Common-Mode dv/dt Noise Canceling Circuit
- Typically Internal 330ns Minimum Dead-Time
- Programmable Turn-On Delay Time Control (Dead-Time)

### Applications

- SMPS
- Motor Drive Inverter
- Fluorescent Lamp Ballast
- HID Ballast

### Description

The FAN7383 is a half-bridge gate-drive IC with shutdown and programmable dead-time control functions for driving MOSFETs and IGBTs that operate up to +600V.

Fairchild's high voltage process and common-mode noise canceling technique give stable operation of high-side drivers under high-dv/dt noise circumstances.

An advanced level-shift circuit allows high-side gate driver operation up to  $V_{S}$ = -9.8V (typical) for  $V_{BS}$ =15V.

The UVLO circuits for both channels prevent malfunction when  $V_{DD}$  and  $V_{BS}$  are lower than the specified threshold voltage.

Output drivers typically source/sink 350mA/650mA, respectively, which is suitable for all kinds of half and full bridge inverter.

14-SOP



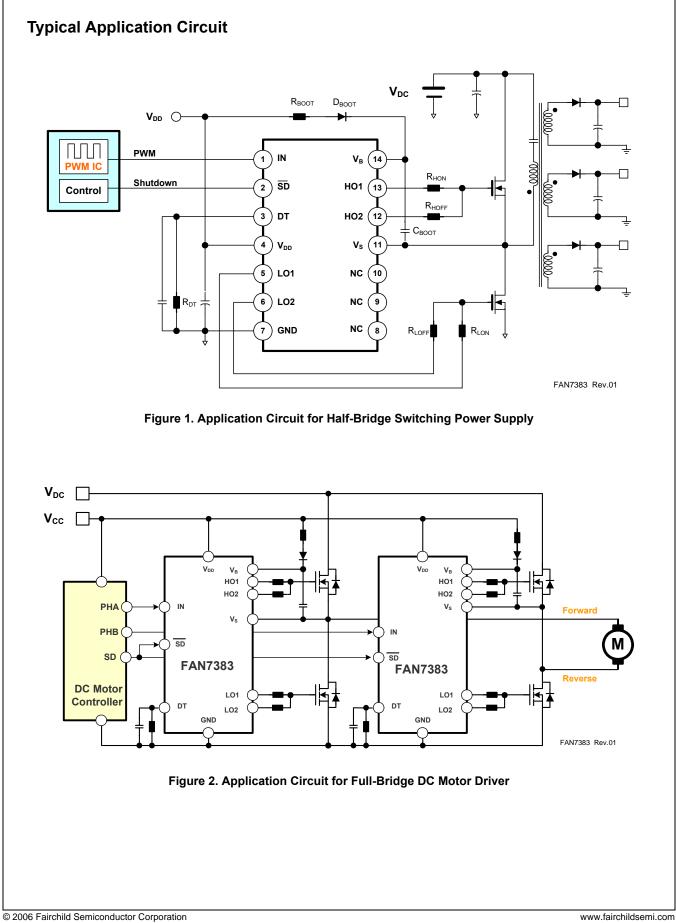
### **Ordering Information**

Part Number	Package	Pb-Free	Operating Temperature Range	Packing Method
FAN7383M <sup>(1)</sup>	14-SOP	Yes	-40°C ~ 125°C	Tube
FAN7383MX <sup>(1)</sup>	14-30F	165	-40 0 ~ 125 0	Tape & Reel

#### Note:

1. These devices passed wave soldering test by JESD22A-111.

February 2007



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FAN7383 Rev. 1.0.3

# Internal Block Diagram

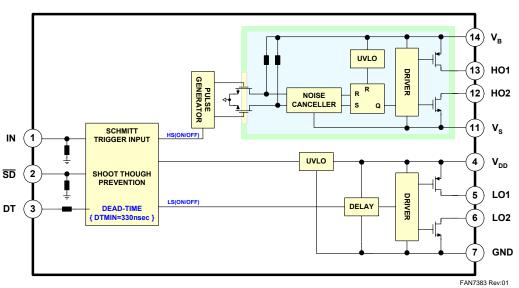
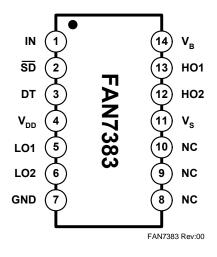


Figure 3. Functional Block Diagram of FAN7383

FAN7383 Half-Bridge Gate-Drive IC

### **Pin Configuration**





### **Pin Definitions**

Pin #	Name	Description	
1	IN	Logic Input for Gate Driver	
2	SD	Logic Input for Shutdown (Active Low)	
3	DT	Programmable Dead-Time Control with External Resistor	
4	V <sub>DD</sub>	Low-Side Supply Voltage	
5	LO1	Low-Side Driver Source Output	
6	LO2	Low-Side Driver Sink Output	
7	GND	Ground	
8	N.C.	Not connected	
9	N.C.	Not connected	
10	N.C.	Not connected	
11	Vs	High-Side Floating Supply Return	
12	HO2	High-Side Driver Sink Output	
13	HO1	High-Side Driver Source Output	
14	V <sub>B</sub>	High-Side Floating Supply	

### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Min.	Max.	Unit
V <sub>S</sub>	High-side offset voltage	V <sub>B</sub> -25	V <sub>B</sub> +0.3	V
V <sub>B</sub>	High-side floating supply voltage	-0.3	625	V
V <sub>HO</sub>	High-side floating output voltage HO1, HO2	V <sub>S</sub> -0.3	V <sub>B</sub> +0.3	V
V <sub>DD</sub>	Low-side and logic fixed supply voltage	-0.3	25	V
V <sub>LO</sub>	Low-side output voltage LO1, LO2	-0.3	V <sub>DD</sub> +0.3	V
V <sub>IN</sub>	Logic input voltage (IN)	-0.3	V <sub>DD</sub> +0.3	V
V <sub>SD</sub>	Shutdown logic input voltage	-0.3	V <sub>DD</sub> +0.3	V
V <sub>DT</sub>	Dead-time control voltage	-0.3	5.0	V
GND	Logic ground	V <sub>DD</sub> -25	V <sub>DD</sub> +0.3	V
dV <sub>S</sub> /dt	Allowable offset voltage slew rate		50	V/ns
P <sub>D</sub> <sup>(2)(3)(4)</sup>	Power dissipation		1.0	W
$\theta_{JA}$	Thermal resistance, junction-to-ambient		110	°C/W
TJ	Junction temperature		150	°C
T <sub>STG</sub>	Storage temperature		150	°C

#### Notes:

- 2. When mounted on 76.2 x 114.3 x 1.6mm PCB. (FR-4 glass epoxy material).
- 3. Please refer to:

JESD51-2: Integral circuits thermal test method environmental conditions - Natural convection JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages

4. Do not exceed  $P_D$  under any circumstances.

### **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Condition	Min.	Max.	Unit
V <sub>B</sub>	High-side floating supply voltage		V <sub>S</sub> +15	V <sub>S</sub> +20	V
V <sub>S</sub>	High-side floating supply offset voltage		6-V <sub>DD</sub>	600	V
V <sub>DD</sub>	Low-side supply voltage		15	20	V
V <sub>HO</sub>	High-side (HO) output voltage		VS	VB	V
V <sub>LO</sub>	Low-side (LO) output voltage		GND	V <sub>DD</sub>	V
V <sub>IN</sub>	Logic input voltage (IN)		GND	V <sub>DD</sub>	V
T <sub>A</sub>	Ambient temperature		-40	125	°C

### **Electrical Characteristics**

 $V_{BIAS}$  ( $V_{DD}$ ,  $V_{BS}$ ) = 15.0V,  $R_{DT}$  = GND,  $T_A$  = 25°C, unless otherwise specified. The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to GND. The  $V_O$  and  $I_O$  parameters are referenced to  $V_S$  and GND and are applicable to the respective outputs HO and LO.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit	
SUPPLY	CURRENT SECTION		•				
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> supply current	V <sub>IN</sub> =0V or 5V		35	90		
I <sub>QDD</sub>	Quiescent V <sub>DD</sub> supply current	$V_{IN}$ =0V or 5V, R <sub>DT</sub> =0 $\Omega$		650	900		
I <sub>SD</sub> <sup>(5)</sup>	V <sub>DD</sub> supply current at shutdown mode	SD=GND		650	900	A	
I <sub>PBS</sub>	Operating V <sub>BS</sub> supply current	f <sub>IN</sub> =20kHz,rms value		400	700	μA	
I <sub>PDD</sub>	Operating V <sub>DD</sub> supply current	$f_{IN}$ =20kHz,rms value, R <sub>DT</sub> =0 $\Omega$		950	1200		
I <sub>LK</sub>	Offset supply leakage current	V <sub>B</sub> =V <sub>S</sub> =600V			10		
POWER S	SUPPLY SECTION						
V <sub>DDUV+</sub> V <sub>BSUV+</sub>	V <sub>DD</sub> and V <sub>BS</sub> supply under-voltage positive going threshold		10.7	11.6	12.5		
V <sub>DDUV-</sub> V <sub>BSUV-</sub>	V <sub>DD</sub> and V <sub>BS</sub> supply under-voltage negative going threshold		10.0	10.8	11.6	V	
V <sub>DDUVH</sub> V <sub>BSUVH</sub>	V <sub>DD</sub> and V <sub>BS</sub> supply under-voltage lockout hysteresis			0.8			
GATE DR	IVER OUTPUT SECTION						
V <sub>OH</sub>	High-level output voltage, $V_{BIAS}$ -V <sub>O</sub>	I <sub>O</sub> =20mA			1.0	V	
V <sub>OL</sub>	Low-level output voltage, V <sub>O</sub>				0.6	V	
I <sub>O+</sub>	Output high short-circuit pulse current	$V_{O}\!\!=\!\!0V,V_{IN}\!\!=\!\!5V$ with PW<10 $\!\mu s$	250	350		mA	
I <sub>O-</sub>	Output low short-circuit pulsed current	$V_{O}\text{=}15V,$ $V_{IN}\text{=}0V$ with PW<10 $\mu\text{s}$	500	650		mA	
$V_{S}$	Allowable negative V <sub>S</sub> pin voltage for IN signal propagation to HO			-9.8	-7.0	V	
LOGIC IN	PUT SECTION (INPUT AND SHUTDOWN	)					
V <sub>IH</sub>	Logic "1" input voltage		2.9			V	
V <sub>IL</sub>	Logic "0" input voltage				1.2	V	
I <sub>IN+</sub>	Logic "1" input bias current	V <sub>IN</sub> =5V		50	100	μΑ	
I <sub>IN-</sub>	Logic "0" input bias current	V <sub>IN</sub> =0V			2.0	μΑ	
SD+	Shutdown "1" input voltage				1.2	V	
SD-	Shutdown "0" input voltage		2.9			V	
R <sub>PD</sub>	Input pull-down resistance			100		KΩ	

Note:

5. This parameter guaranteed by design.

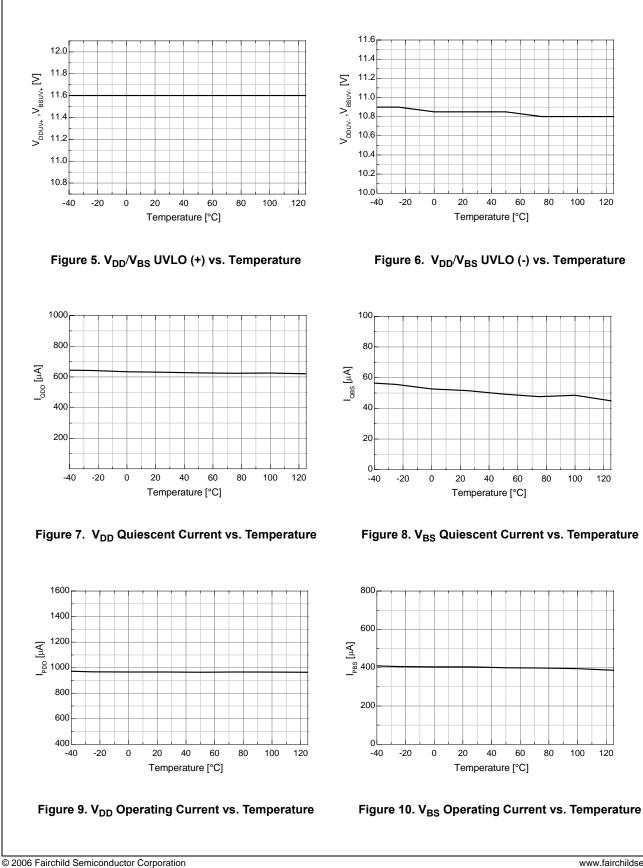
### Dynamic Electrical Characteristics

 $V_{BIAS}$  ( $V_{DD}$ ,  $V_{BS}$ ) = 15.0V,  $V_{S}$  = GND,  $C_{L}$ =1000pF,  $R_{DT}$  = GND, and  $T_{A}$  = 25°C, unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
t <sub>ON</sub>	Turn-on propagation delay	V <sub>S</sub> =0V		500	670	
t <sub>OFF</sub>	Turn-off propagation delay	V <sub>S</sub> =0V or 600V <sup>(5)</sup>		170	250	
t <sub>R</sub>	Turn-on rise time			50	100	ns
t <sub>F</sub>	Turn-off fall time			30	80	
t <sub>SD</sub> <sup>(5)</sup>	Shutdown propagation delay			100	180	
DT1,	Dead-time LO OFF to HO ON and HO	R <sub>DT</sub> =0Ω	250	330	420	ns
DT2	OFF to LO ON	R <sub>DT</sub> =200KΩ	1.20	1.68	2.30	μs
DMT	Dead-time matching	R <sub>DT</sub> =0Ω		0	60	200
		R <sub>DT</sub> =200KΩ		0	150	ns

#### Note:

5. These parameters guaranteed by design.

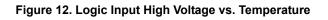


**Typical Characteristics** 

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#### Typical Characteristics (Continued) 3.0<sub>1</sub> 100 2.5 80 2.0 ا<sub>ا^+</sub> [پط] ≥ ><sup>±</sup> 1.5 60 40 1.0 20 0.5 0 0.0 -40 -20 0 20 40 60 80 100 120 -40 -20 0 20 40 60 80 100 Temperature [°C] Temperature [°C]





120

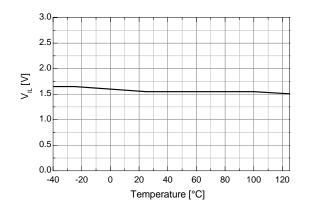
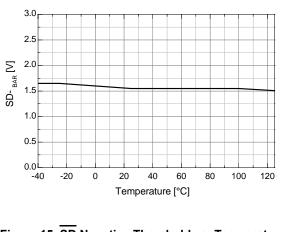


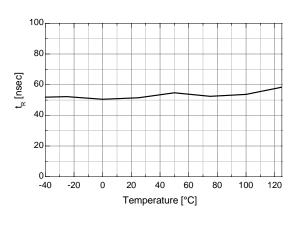
Figure 13. Logic Input Low Voltage vs. Temperature



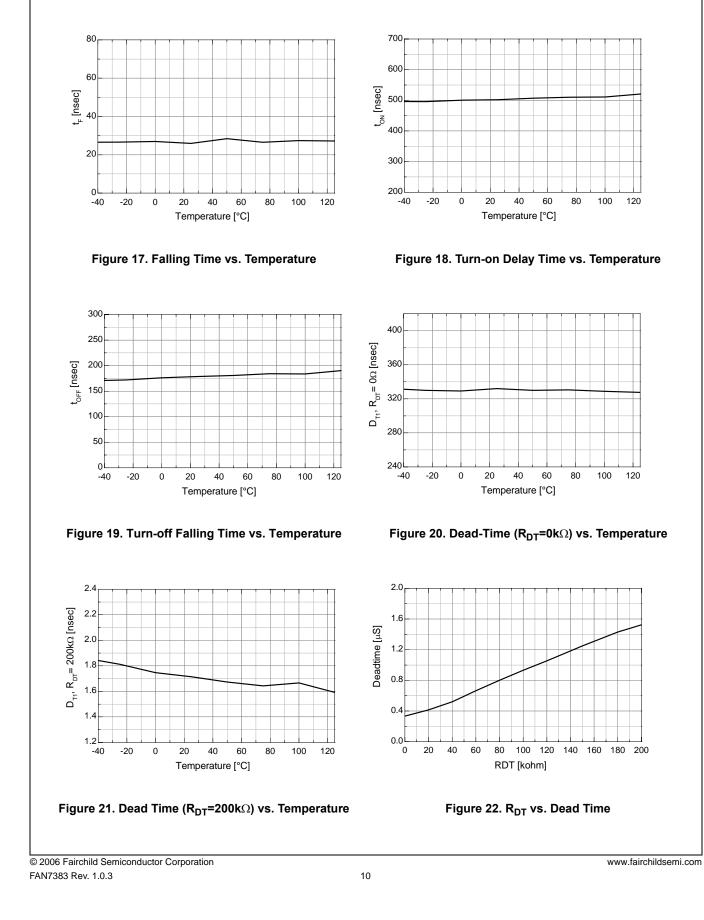


3.0 2.5 ∑ 2.0 SD+ BAR 1.5 1.0 0.5 0.0 -40 -20 0 20 40 60 80 100 120 Temperature [°C]

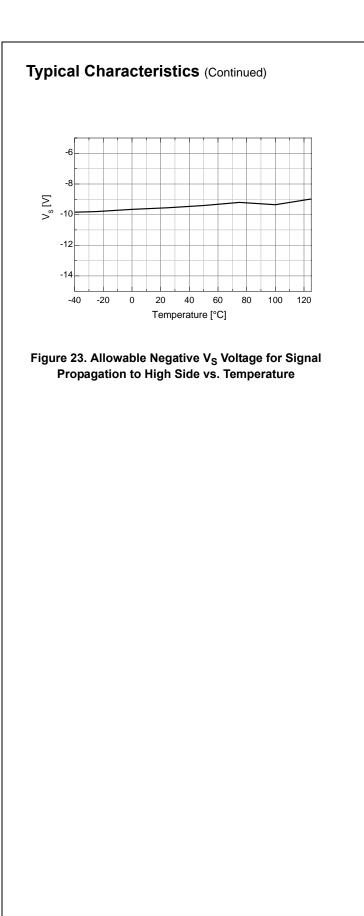
Figure 14. SD Positive Threshold vs. Temperature

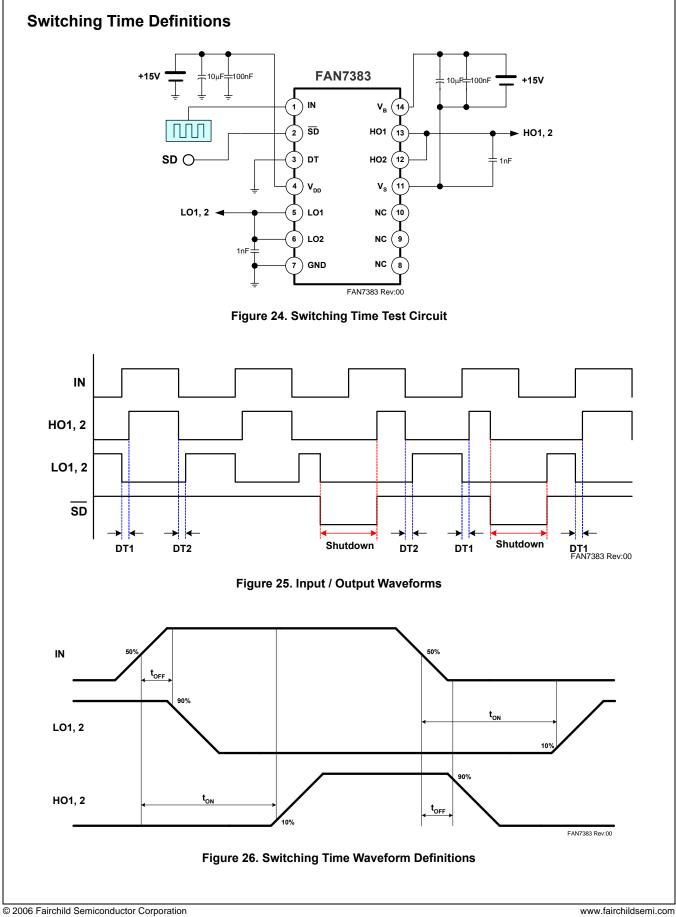




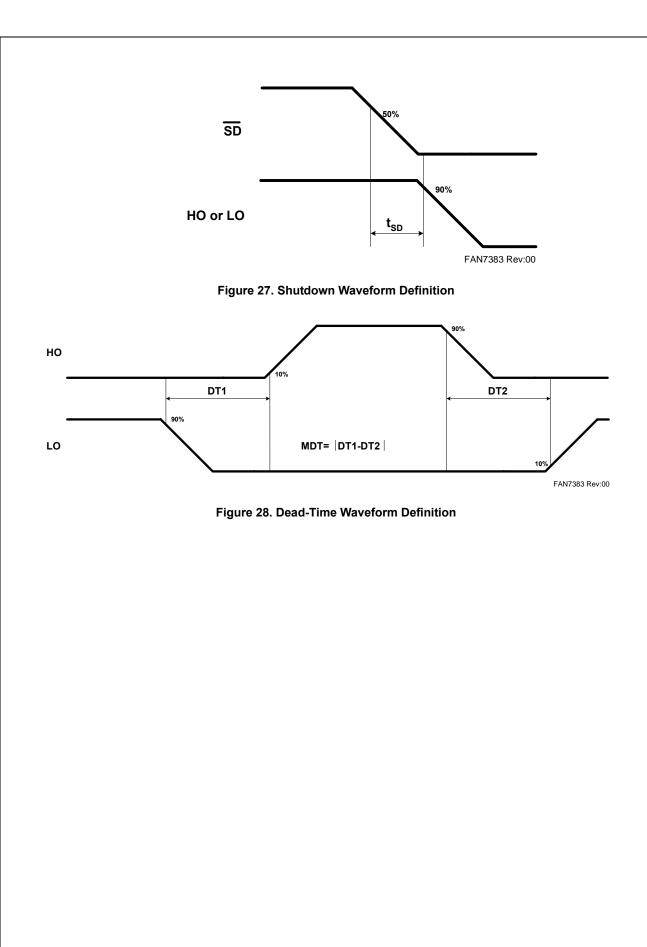


Typical Characteristics (Continued)





FAN7383 Half-Bridge Gate-Drive IC



### **Typical Application Information**

#### 1. Normal Operating Consideration

The FAN7383 is a single PWM input half-bridge gatedrive IC with programmable dead-time and shutdown function.

The dead-time is set with a resistor ( $R_{DT}$ ) at the DT pin. The wide dead-time programming range provides the flexibility to optimize drive signal timing for a selection of switching devices (MOSFET or IGBT) and applications.

The turn-on time delay circuitry (Dead-Time) accommodates resistor values from  $0\Omega$  to  $200k\Omega$  with a dead-time proportional to the R<sub>DT</sub> resistance.

Grounding the DT pin programs the FAN7383 to drive both outputs with minimum dead time.

If the SD pin voltage decrease below 1.2V in normal operation, the IC enters the shutdown mode.

#### 2. Under-Voltage Lockout (UVLO)

The FAN7383 has an under-voltage lockout (UVLO) protection circuitry for high and low side channels to prevent malfunction when  $V_{DD}$  or  $V_{BS}$  is lower than the specified threshold voltage. The UVLO circuitry monitors the supply voltage ( $V_{DD}$ ) and bootstrap capacitor voltage ( $V_{BS}$ ) independently.

#### 3. Layout Consideration

For optimum performance of high- and low-side gate drivers, cannot be achieved without taking due considerations must be taken during printed circuit board (PCB) layout.

#### 3.1 Supply Capacitors

If the output stages are able to quickly turn on the switching device with high value of current, the supply capacitors must be placed as close as possible to the device pins (V<sub>DD</sub> and GND for the ground-tied supply, V<sub>B</sub> and V<sub>S</sub> for the floating supply) to minimize parasitic inductance and resistance.

#### 3.2 Gate Drive Loop

Current loops behave like an antenna, able to receive and transmit noise. To reduce the noise coupling/ emission and improve the power switch turn-on and off performances, gate drive loops must be reduced as much as possible.

#### 3.3 Ground Plane

Ground plane must not be placed under or nearby the high-voltage floating side to minimize noise coupling.

### Package Dimensions

#### 14-SOP

Dimensions are in millimeters unless otherwise noted.

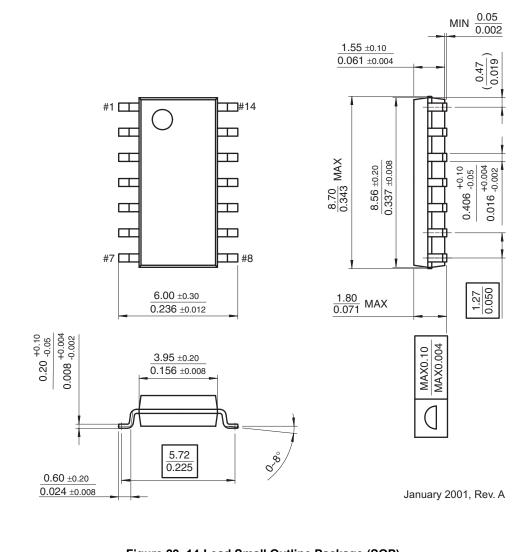


Figure 29. 14-Lead Small Outline Package (SOP)



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FAN7383 Half-Bridge Gate-Drive IC

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